



CMKD6001

**SURFACE MOUNT ULTRAmi™
TRIPLE ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES**



SOT-363 CASE

**Central™
Semiconductor Corp.**

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmi™ surface mount package, designed for switching applications requiring extremely low leakage.

MARKING CODE: K01

MAXIMUM RATINGS: (T_A=25°C)

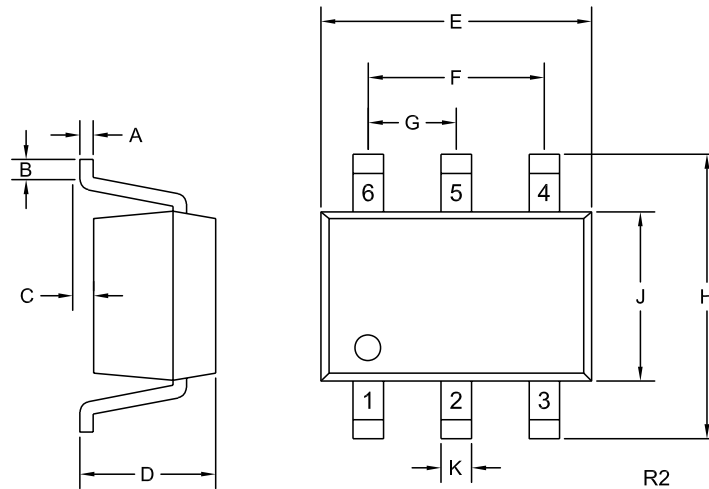
Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Forward Surge Current, tp=1.0µs
Forward Surge Current, tp=1.0s
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V _R	75	V
V _R RM	100	V
I _F	250	mA
I _F RM	500	mA
I _F SM	4.0	A
I _F SM	1.0	A
P _D	250	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	500	°C/W

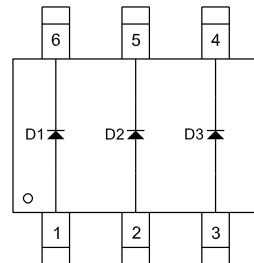
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =75V		500	pA
BV _R	I _R =100µA	100		V
V _F	I _F =1.0mA		0.85	V
V _F	I _F =10mA		0.95	V
V _F	I _F =100mA		1.1	V
C _T	V _R =0, f=1.0MHz		2.0	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω Rec. to 1.0mA		3.0	µs

SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) ANODE D1
- 2) ANODE D2
- 3) ANODE D3
- 4) CATHODE D3
- 5) CATHODE D2
- 6) CATHODE D1

MARKING CODE: K01

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)